
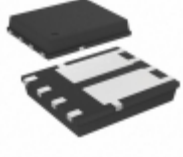
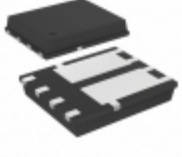

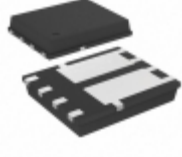

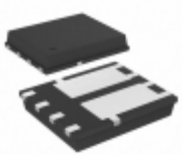
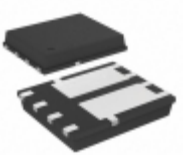
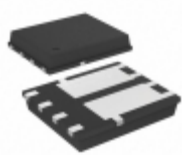
	<h2>SI7956DP-T1-GE3</h2>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI7956DP-T1-GE3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET 2N-CH 150V 2.6A PPAK SO-8</p> <p><b>Datenblätter:</b>  <a href="#">SI7956DP-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 801660 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">SI7956DP-T1-GE3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET 2N-CH 150V 2.6A PPAK SO-8
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	801660 pcs Stock
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.4W
Verpackung / Gehäuse	PowerPAK® SO-8 Dual
Supplier Device-Gehäuse	PowerPAK® SO-8 Dual
Typ FET	2 N-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	150V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.6A
Rds On (Max) @ Id, Vgs	105 mOhm @ 4.1A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	26nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)












SI7956DP-T1-GE3 ist neu im Original, Suche SI7956DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7956DP-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7956DP-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI7956DP-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 150V 2.6A PPAK SO-8</p>	 <p><b>SI7956DP-T1-E3</b> Vishay / Siliconix MOSFET 2N-CH 150V 2.6A PPAK SO-8</p>	 <p><b>SI7956DP-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 150V 2.6A PPAK SO-8</p>	 <p><b>SI7958DP-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 40V 7.2A PPAK SO-8</p>
 <p><b>SI7958DP</b> SI SI7958DP SI</p>	 <p><b>SI7958DP-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 40V 7.2A PPAK SO-8</p>	 <p><b>SI7949DP-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET 2P-CH 60V 3.2A PPAK SO-8</p>	 <p><b>SI7958DP-T1-GE3</b> Vishay / Siliconix MOSFET 2N-CH 40V 7.2A PPAK SO-8</p>

### heiße Teile

Mehr

 SI7922DN-T1-GE3	 SI7922DN-T1-GE3	 SI7923DN-T1-E3	 SI7923DN-T1-E3	 SI7923DN-T1-GE3
 SI7923DN-T1-GE3	 SI7938DP-T1-GE3	 SI7938DP-T1-GE3	 SI7940DP	 SI7940DP-T1-E3
 SI7940DP-T1-E3	 SI7941DP-T1-E3	 SI7941DP-T1-GE3	 SI7942DP	 SI7942DP-T1-E3
 SI7942DP-T1-E3	 SI7942DP-T1-GE3	 SI7942DP-T1-GE3	 SI7945DP-T1-E3	 SI7945DP-T1-E3
 SI7946DP	 SI7946DP-T1-E3	 SI7946DP-T1-E3	 SI7948DP	 SI7948DP-T1-E3
 SI7949DP-T1-GE3	 SI7949DP-T1-GE3	 SI7956DP-T1-GE3	 SI7958DP	 SI7958DP-T1-E3
 SI7958DP-T1-E3	 SI7958DP-T1-GE3	 SI7958DP-T1-GE3	 SI7960DP-T1-E3	 SI7960DP-T1-E3
 SI7960DP-T1-GE3	 SI7960DP-T1-GE3	 SI7964DP	 SI7964DP-T1-GE3	 SI7964DP-T1-GE3
 SI7970DP	 SI7970DP-T1-E3	 SI7980DP-T1-E3	 SI7980DP-T1-E3	 SI7980DP-T1-GE3
 SI7980DP-T1-GE3	 SI7997DP-T1-GE3	 SI7997DP-T1-GE3	 SI7998DP-T1-GE3	 SI7998DP-T1-GE3

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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